AUTOMOTIVE

RoHS

COMPLIANT

HALOGEN FREE



# Vishay Semiconductors

# Hyperfast Rectifier, 1 A FRED Pt®



#### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	1 A			
$V_{R}$	100 V			
V <sub>F</sub> at I <sub>F</sub>	0.68 V			
t <sub>rr</sub>	25 ns			
T <sub>J</sub> max.	175 °C			
Package	SMA (DO-214AC)			
Circuit configuration	Single			

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating **Terminals:** matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub>		100	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 158 °C	1	^	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	50	Α	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C	



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	$V_{BR}, V_{R}$	I <sub>R</sub> = 100 μA	100	-	-			
Forward valtage per diade	\/_	I <sub>F</sub> = 1 A	-	0.82	0.90	V		
Forward voltage, per diode	V <sub>F</sub>	VF	VF	I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C	-	0.68	0.76	
Reverse leakage current, per diode	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	μΑ		
		T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	0.6	8			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 100 V	-	8.5	-	pF		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A, } dI_F/dt =$	$= 50 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	-	24	-	
Davage good time	t <sub>rr</sub>	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}$	A, I <sub>rr</sub> = 0.25 A	-	-	25	
Reverse recovery time		T <sub>J</sub> = 25 °C		-	15.2	-	ns
		T <sub>J</sub> = 125 °C		-	21	-	
Dools was as your as weart		T <sub>J</sub> = 25 °C	$I_F = 1 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 100 \text{ V}$	-	1.38	-	^
Peak recovery current	IRRM	T <sub>J</sub> = 125 °C		-	2	-	Α
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	10.6	-	nC
		T <sub>J</sub> = 125 °C		-	21	-	110

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C
Thermal resistance, junction to lead	R <sub>thJL</sub>	Device mounted on PCB with 2 x 3.5 mm soldering lands	-	11	21	°C/W
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Device mounted on PCB with recommended pad size	-	-	125	°C/W
Approximate weight				0.07		g
Approximate weight				0.002		oz.
Marking device		Case style SMA (DO-214AC)		1	H1	

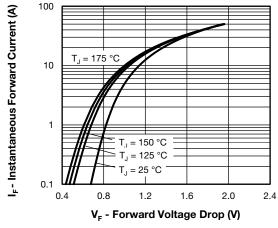


Fig. 1 - Typical Forward Voltage Drop Characteristics

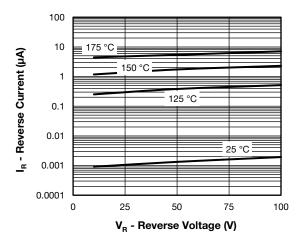


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

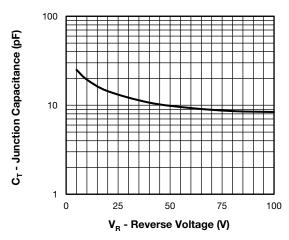


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

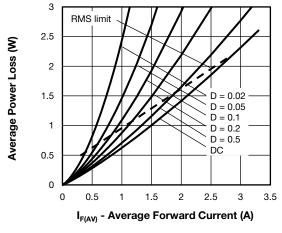


Fig. 5 - Forward Power Loss Characteristics

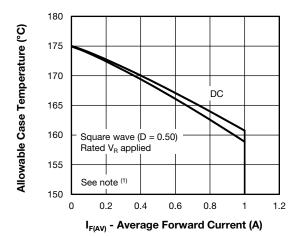


Fig. 4 - Maximum Allowable Case Temperature vs.
Average Forward Current

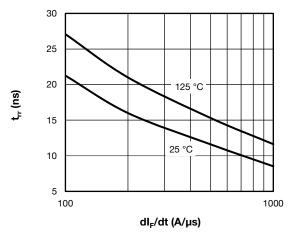


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

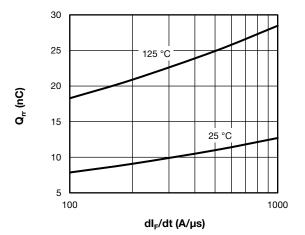
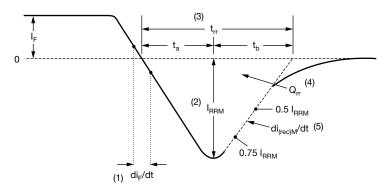


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 5)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>BBM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

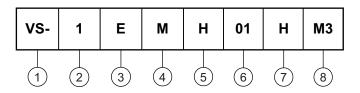
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- Current rating (1 = 1 A)
- Circuit configuration:

E = single diode

4 - M = SMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (01 = 100 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-1EMH01HM3/5AT	7500	7500	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95400</u>				
Part marking information	www.vishay.com/doc?95472			
Packaging information	www.vishay.com/doc?95404			
SPICE model	www.vishay.com/doc?96376			



# **SMA**

### **DIMENSIONS** in inches (millimeters)

### **DO-214AC (SMA)**



### Mounting Pad Layout





## **Legal Disclaimer Notice**

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